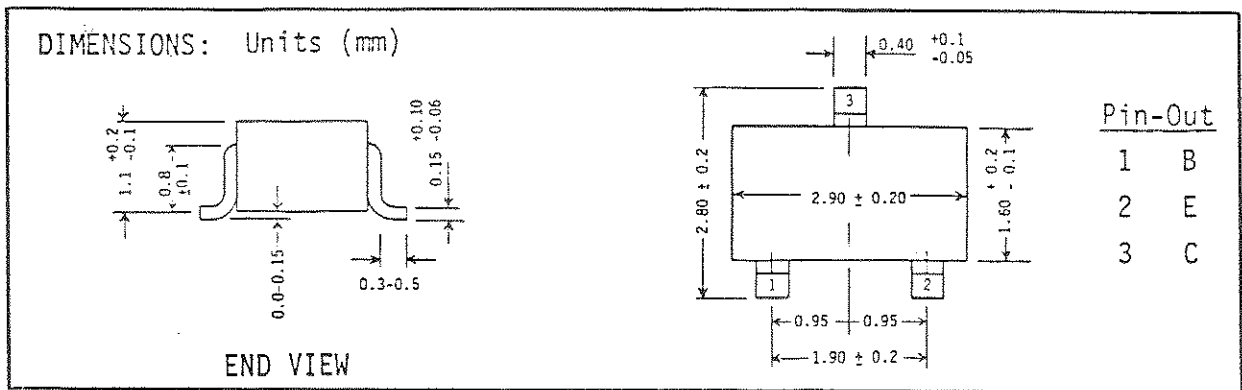


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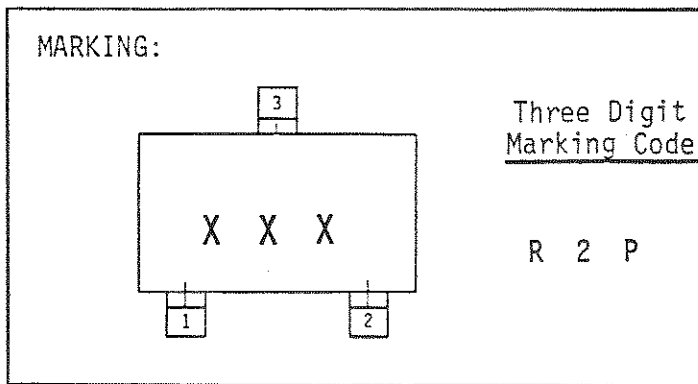
SUBJECT  
SOT-23 TRANSISTOR, PNP, SILICON

ABSOLUTE MAXIMUM RATINGS: (Ta = 25°C)

Collector-Base Voltage	V <sub>CB0</sub>	50 V
Collector-Emitter Voltage	V <sub>CE0</sub>	50 V
Emitter-Base Voltage	V <sub>EB0</sub>	3 V
Collector Current	I <sub>C</sub>	200 mA
Power Dissipation-Free Air	P <sub>D</sub>	200 mW
Power Dissipation-Ceramic Substrate	P <sub>D</sub>	350 mW
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150 °C
Solder Temperature (10 seconds)		260 °C



THE JAPANESE STYLE SC-59 PACKAGE



PACKAGING:

- \_\_\_ BULK, 500 per BAG
- \_\_\_ MAGAZINES OF 50 EACH
- \_\_\_ 8mm T&R, T- 146 3K/REEL
- \_\_\_ 8mm T&R, T- 147 3K/REEL
- \_\_\_ 8mm T&R, T- 24610K/REEL
- \_\_\_ 8mm T&R, T- 24710K/REEL

REMARKS: PROCESS: A-22 Thermal Resistance R<sub>θJA</sub> 625 °C/Watt  
FREE AIR, T<sub>A</sub> = 25°C



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SUBJECT TRANSISTOR, PNP ,SILICON SOT-23	DATE January 14, 1987

ELECTRICAL CHARACTERISTICS: (Ta = 25°C Unless Otherwise Specified)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BV <sub>CB0</sub>	I <sub>C</sub> = 100 $\mu$ A	50			V
BV <sub>CEO</sub>	I <sub>C</sub> = 1.0 mA	50			V
I <sub>CB0</sub>	V <sub>CB</sub> = 45 V		0.7	100	nA
I <sub>CEO</sub>	V <sub>CE</sub> = 40 V		0.7	100	nA
I <sub>EB0</sub>	V <sub>EB</sub> = 4.5 V		0.7	100	nA
h <sub>FE</sub>	I <sub>C</sub> = 100 $\mu$ A, V <sub>CE</sub> = 5.0 V	150		500	
h <sub>FE</sub>	I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 5.0 V	150			
h <sub>FE</sub>	I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 V	150			
V <sub>CE(SAT)</sub>	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1.0 mA		0.05	0.30	V
V <sub>BE(ON)</sub>	I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 5.0 V		0.60	0.85	V
f <sub>T</sub>	I <sub>C</sub> = 500 $\mu$ A, V <sub>CE</sub> = 5 V, f = 20 MHz	40			MHz
h <sub>fe</sub>	I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 5 V, f = 1.0KHz	150		600	
C <sub>cb</sub>	V <sub>CB</sub> = 5.0 V, I <sub>E</sub> = 0, f = 100 KHz		5.0	6.0	pF
NF	I <sub>C</sub> = 20 $\mu$ A, V <sub>CE</sub> = 5.0V, R <sub>s</sub> =10K $\Omega$ f = 10 Hz to 15.7 KHz			3.0	dB
NF	I <sub>C</sub> = 100 $\mu$ A, V <sub>CE</sub> = 5.0V, R <sub>s</sub> =3K $\Omega$ f = 1.0 KHz			3.0	dB

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MASTER

APPROVAL  
*ARR* 10/12/84

CHECK  
✓

DESIGN